TEXAS INSTRUMENTS

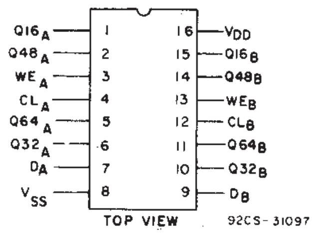
Data sheet acquired from Harris Semiconductor
SCHS075

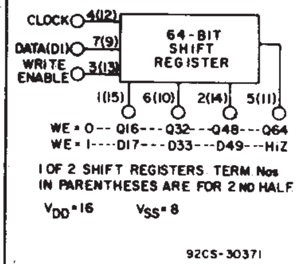
CD4517B Types

CMOS Dual 64-Stage Static Shift Register

High-Voltage Types (20-Volt Rating)

TERMINAL ASSIGNMENT





TERMINAL ASSIGNMENT

■ CD4517B dual 64-stage static shift register consists of two independent registers each having a clock, data, and write enable input and outputs accessible at taps following the 16th, 32nd, 48th, and 64th stages. These taps also serve as input points allowing data to be inputted at the 17th, 33rd, and 49th stages when the write enable input is a logic 1 and the clock goes through a low-to-high transition. The truth table indicates how the clock and write enable inputs control the operation of the CD4517B. Inputs at the intermediate taps allow entry of 64 bits into the register with 16 clock pulses. The 3-state outputs permit connection of this device to an external bus.

The CD4517B is supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Low quiescent current – 10 nA/pkg (typ.) at $V_{DD} = 5$ V
- Clock frequency 12 MHz (typ.) at $V_{DD} = 10$ V
- Schmitt trigger clock inputs allow operation with very slow clock rise and fall times
- Capable of driving two low-power TTL loads, one low-power Schottky TTL load, or two HTL loads
- Three-state outputs
- 100% tested for quiescent current at 20 V
- Standardized, symmetrical output characteristics
- 5-V, 10-V and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative **Standard No. 13B**, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Time-delay circuits
- Scratch-pad memories
- General-purpose serial shift-register applications

MAXIMUM RATINGS, ***Absolute-Maximum Values:***

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) .... −0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS .... −0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT .... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = −55°C to +100°C 500mW
For T_A = +100°C to +125°C .... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) .... −55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) .... −65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max .... +265°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

TRUTH TABLE

Clock	Write Enable	Data	Stage 16 Tap	Stage 32 Tap	Stage 48 Tap	Stage 64 Tap
0	0	X	Q16	Q32	Q48	Q64
0	1	X	Z	Z	Z	Z
1	0	X	Q16	Q32	Q48	Q64
1	1	X	Z	Z	Z	Z
⟋	0	DI In	Q16	Q32	Q48	Q64
⟋	1	DI In	D17 In	D33 In	D49 In	Z
⟍	0	X	Q16	Q32	Q48	Q64
⟍	1	X	Z	Z	Z	Z

X = Don't Care   Z = High Impedance

3
COMMERCIAL CMOS HIGH VOLTAGE ICs

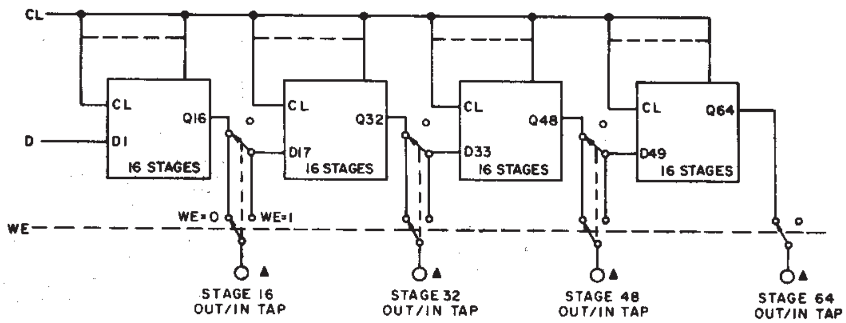
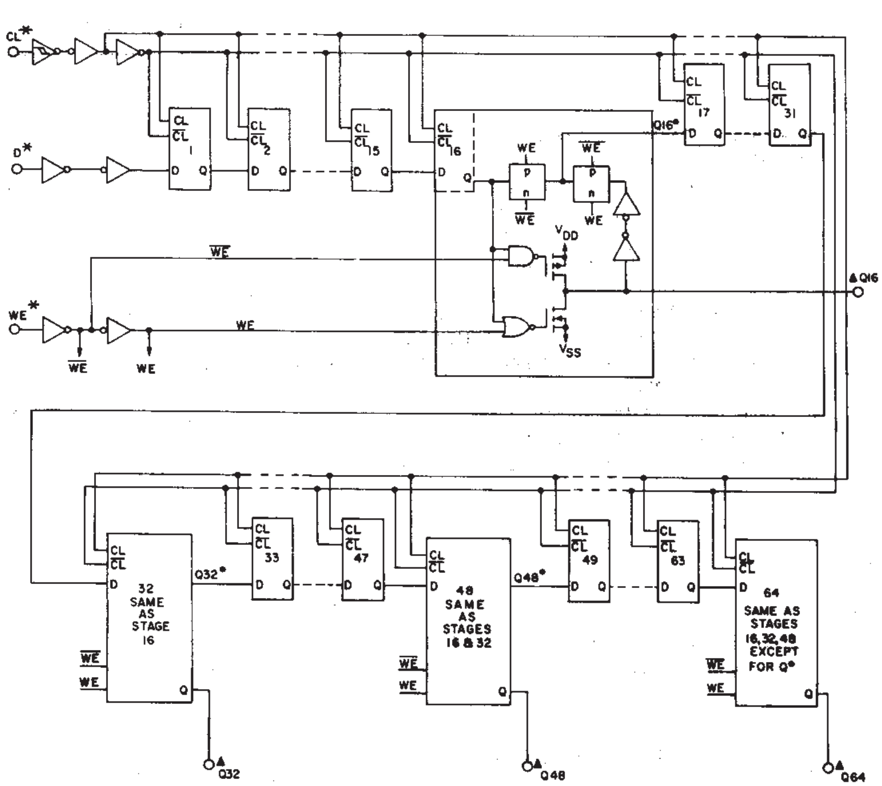
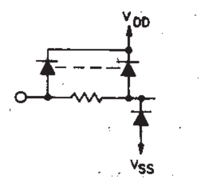
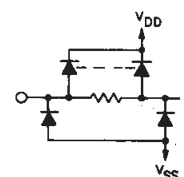


Fig. 1—CD4517B functional block diagram (one half).





▲ PROTECTED BY CMOS PROTECTION NETWORK



* PROTECTED BY CMOS PROTECTION NETWORK

Fig. 2—CD4517B logic block diagram (one half).

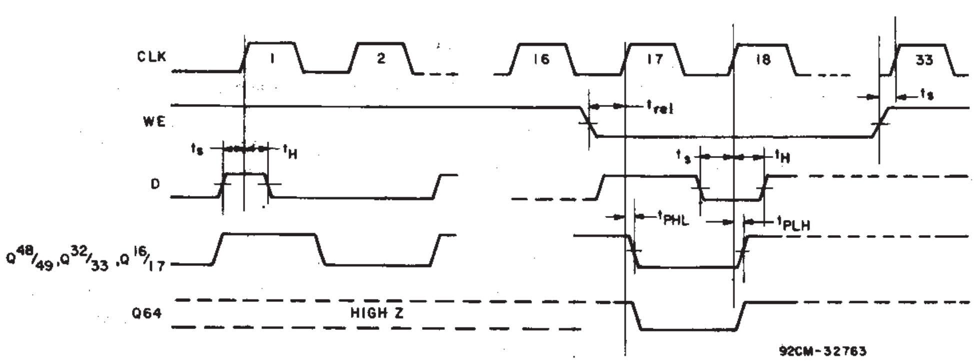


Fig. 3—Dynamic test waveforms.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	μA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm10^{-5}$	±0.1	μA
3-State Output Leakage Current I_{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	–	$\pm10^{-4}$	±0.4	μA

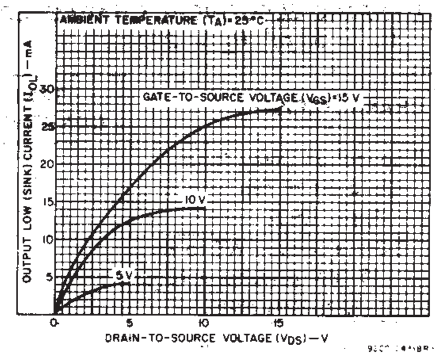


Fig. 4—Typical n-channel output low (sink) current characteristics.

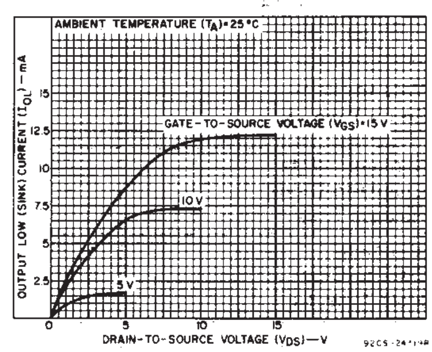


Fig. 5—Minimum n-channel output low (sink) current characteristics.

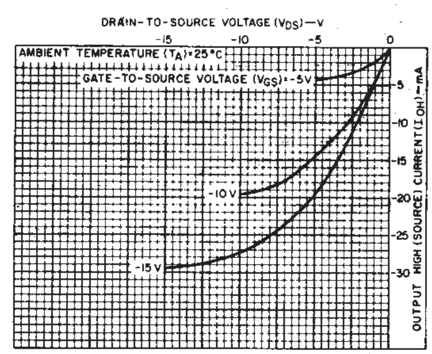


Fig. 6—Typical p-channel output high (source) current characteristics.

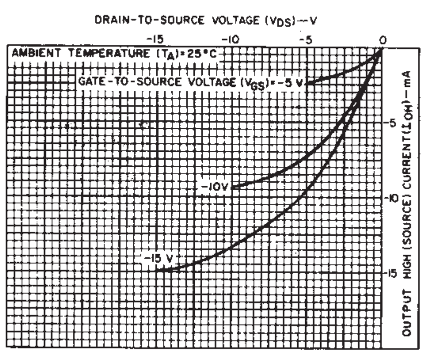


Fig. 7—Minimum p-channel output high (source) current characteristics.

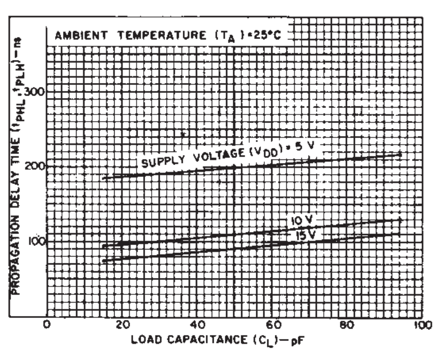


Fig. 8—Typical propagation delay time as a function of load capacitance.

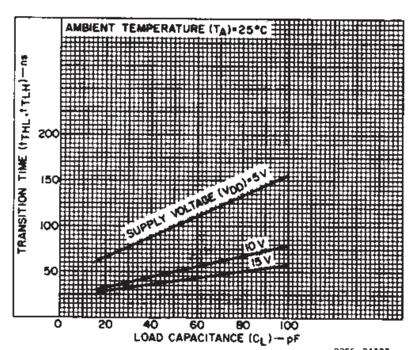


Fig. 9—Typical transition time a a function of load capacitance.

3

COMMERCIAL CMOS HIGH VOLTAGE ICs

DYNAMIC ELECTRICAL CHARACTERISTICS *at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ*

CHARACTERISTIC	TEST CONDITIONS	V_{DD} (V)	LIMITS Min.	LIMITS Typ.	LIMITS Max.	UNITS
Propagation Delay Time: CL to Bit 16 Tap t_{PHL}, t_{PLH}		5	—	200	400	ns
		10	—	110	220	
		15	—	90	180	
3-State Output, WE to Bit 16 Tap t_{PHZ}, t_{PLZ}; t_{PZH}, t_{PZL} (See Note)		5	—	75	150	ns
		10	—	40	80	
		15	—	30	60	
Output Transition Time t_{THL}, t_{TLH}		5	—	100	200	ns
		10	—	50	100	
		15	—	40	80	
Write Enable-to-Clock Setup Time		5	0	−50	—	ns
		10	0	−25	—	
		15	0	−15	—	
Data-to-Clock Setup Time, t_s		5	20	0	—	ns
		10	10	0	—	
		15	10	0	—	
Minimum Write Enable-to-Clock Release Time		5	—	50	100	ns
		10	—	25	50	
		15	—	20	40	
Minimum Data-to-Clock Hold Time, t_H		5	—	100	200	ns
		10	—	50	100	
		15	—	25	50	
Minimum Clock Pulse Width, t_W		5	—	90	180	ns
		10	—	40	80	
		15	—	25	50	
Maximum Clock Input Frequency, f_{CL}		5	3	6	—	MHz
		10	6	12	—	
		15	8	15	—	
Maximum Clock Input Rise or Fall Time, t_{fCL} t_{rCL}		5	UNLIMITED			μs
		10				
		15				
Input Capacitance C_{IN}	Any Input		—	5	7.5	pF

NOTE: Measured at the point of 10% change in output with an output load of 50 pF, RL = 1 kΩ to V_{DD} for t_{PZL}, t_{PLZ} and R_L = 1 kΩ to V_{SS} for t_{PZH}, t_{PHZ}.

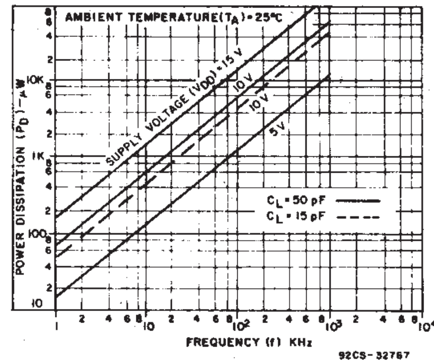


Fig. 10—Typical power dissipation as a function of frequency.

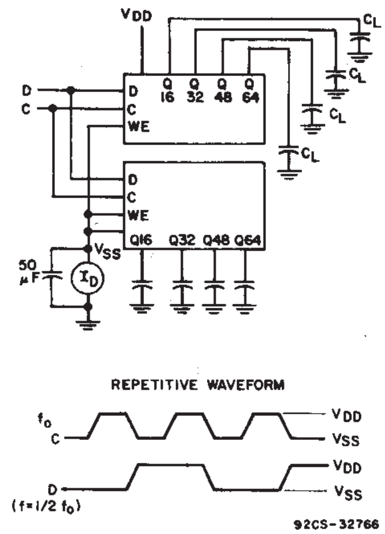


Fig. 11—Dynamic power dissipation test circuit and waveforms.

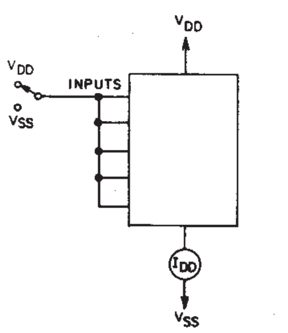


Fig. 12—Quiescent-device-current test circuit.

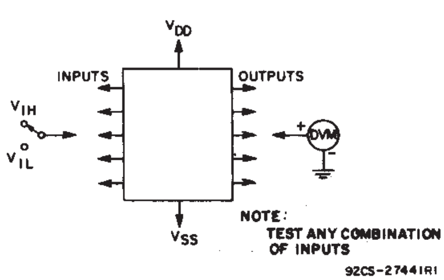


Fig. 13—Input-voltage test circuit.

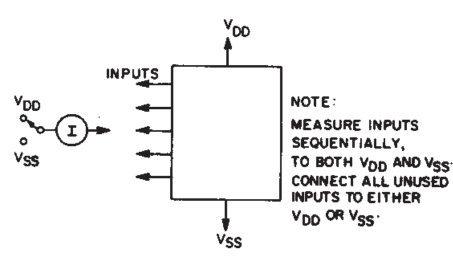
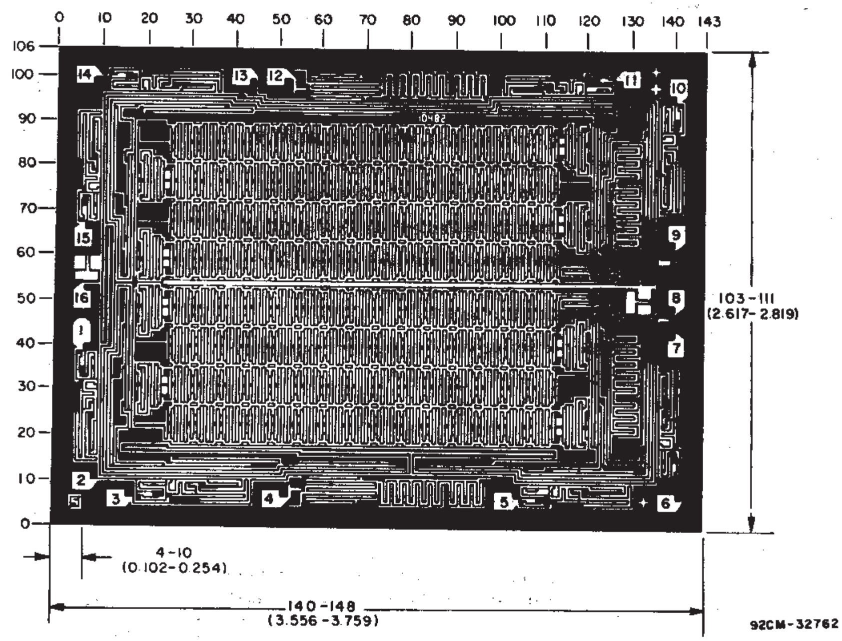


Fig. 14—Input current test circuit.



Dimensions and pad layout for CD4517B.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated